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Vishay Siliconix

# Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V <sub>DS</sub> (V)	40
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0034
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0043
I <sub>D</sub> (A)	75
Configuration	Single

#### **FEATURES**

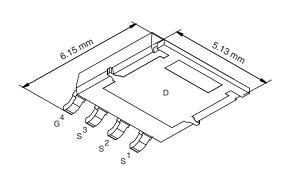
- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested
- AEC-Q101 Qualified<sup>c</sup>
- Material categorization:
  For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

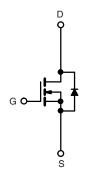




ROHS COMPLIANT HALOGEN FREE

#### PowerPAK® SO-8L Single





N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ422EP-T1-GE3

ABSOLUTE MAXIMUM RATING	<b>S</b> (T <sub>C</sub> = 25 °C, unles	s otherwise noted	)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		$V_{DS}$	40	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	V
Continuous Drain Current	T <sub>C</sub> = 25 °C	1	75	
Continuous Drain Current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	62	
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	75	Α
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	300	
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	46	
Single Pulse Avalanche Energy	L = 0.1 IIII	E <sub>AS</sub>	105	mJ
Mayimum Bayyar Dissination?	T <sub>C</sub> = 25 °C	D	83	W
Maximum Power Dissipation <sup>a</sup>	m Power Dissipation <sup>a</sup> $T_C = 125 ^{\circ}C$ $P_D$ 27	27	vv	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C
Soldering Recommendations (Peak Tempera	ature) <sup>d, e</sup>		260	C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>b</sup>	$R_{thJA}$	65	°C/W
Junction-to-Case (Drain)		$R_{thJC}$	1.8	C/VV

#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. When mounted on 1" square PCB (FR-4 material).
- c. Parametric verification ongoing.
- d. See solder profile (<u>www.vishav.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static	<u>'</u>	,					
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = 250 μA	40	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	- V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2.0	2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V	-	-	1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	-	-	50	μΑ
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 18 A	-	0.0028	0.0034	
Drain-Source On-State Resistance <sup>a</sup>	ь	V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 16 A	-	0.0035	0.0043	Ω
Dialii-Source Oii-State nesistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 18 A, T <sub>J</sub> = 125 °C	-	-	0.0071	22
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 18 A, T <sub>J</sub> = 175 °C	-	-	0.0089	
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 18 A	-	117	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	3730	4660	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 20 V, f = 1 MHz	-	553	691	рF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	223	278	
Total Gate Charge <sup>c</sup>	Qg			-	67	100	
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, I_D = 10 \text{ A}$	-	11.25	-	nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	10.31	-	
Gate Resistance	R <sub>g</sub>		f = 1 MHz	0.30	0.63	1.10	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	13	19	
Rise Time <sup>c</sup>	t <sub>r</sub>		= 20 V, $R_L = 20 \Omega$	-	10	15	no
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A},$	$V_{GEN} = 10 \text{ V}, R_g = 6 \Omega$	-	29	44	ns
Fall Time <sup>c</sup>	t <sub>f</sub>			-	8	12	
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	300	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> :	= 12 A, V <sub>GS</sub> = 0	-	0.75	1.1	V

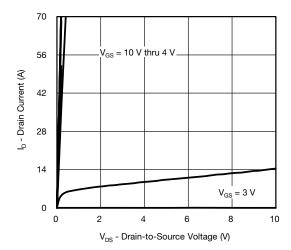
### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

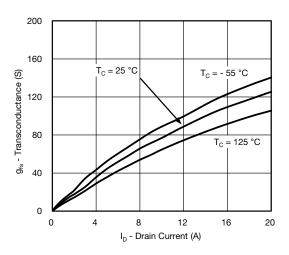
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



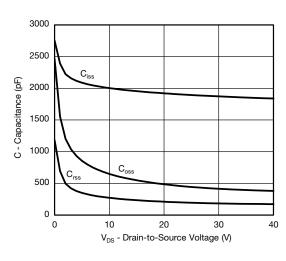
# TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



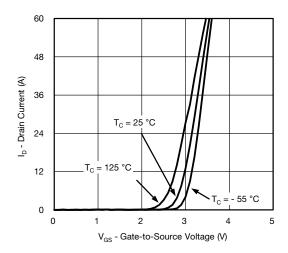
### **Output Characteristics**



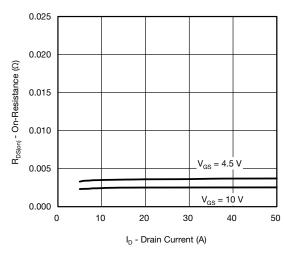
### Transconductance



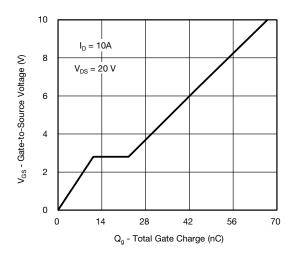
### Capacitance



### **Transfer Characteristics**

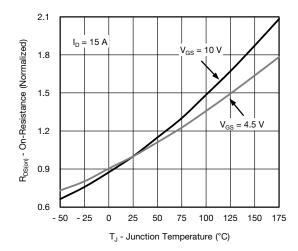


On-Resistance vs. Drain Current

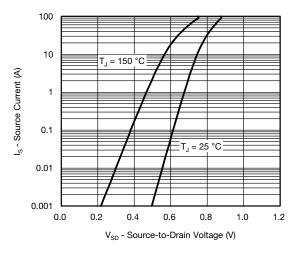




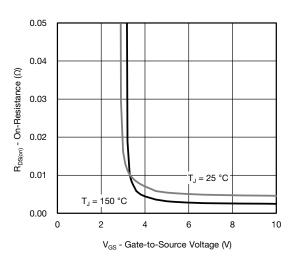
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



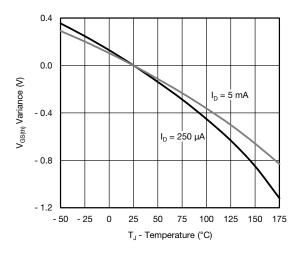
On-Resistance vs. Junction Temperature



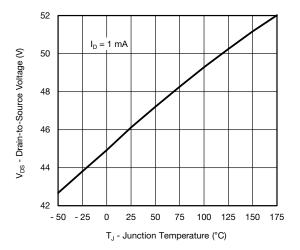
**Source Drain Diode Forward Voltage** 



On-Resistance vs. Gate-to-Source Voltage



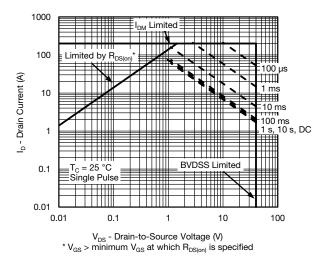
Threshold Voltage



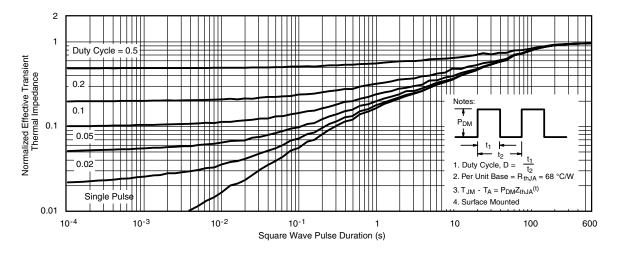
Drain Source Breakdown vs. Junction Temperature



# **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



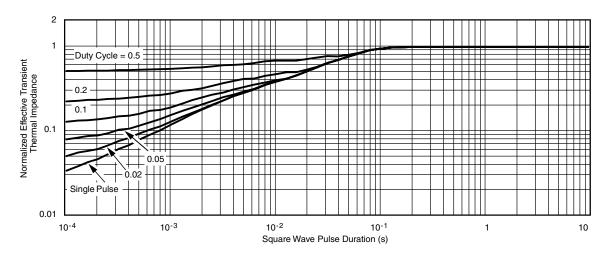
### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

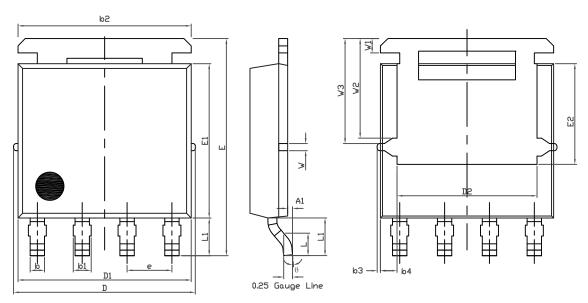
#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

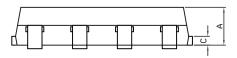
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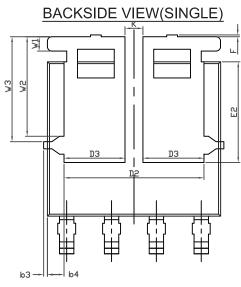


# PowerPAK® SO-8L Case Outline 2



**TOPSIDE VIEW** 





BACKSIDE VIEW(DUAL)



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DIM		MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN. NOM.		MAX.		
Α	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094			0.004			
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC		0.050 BSC				
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
K		0.51			0.020			
W		0.23			0.009			
W1		0.41			0.016			
W2	2.82			0.111				
W3		2.96			0.117			
q	0°	-	10°	0°	-	10°		

ECN: S19-0643-Rev. B, 05-Aug-2019

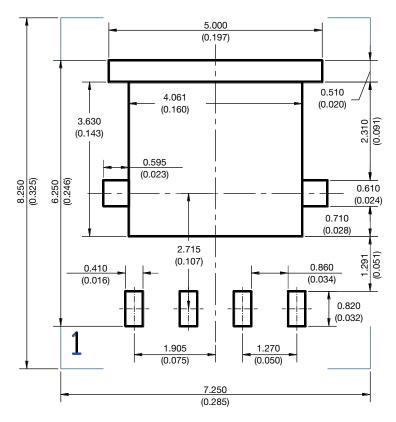
DWG: 6044

### Note

• Millimeters will gover



## RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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